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National Semiconductor

DS15BR400/DS15BR401 4-Channel LVDS Buffer/Repeater with Pre-Emphasis

General Description

The DS15BR400/DS15BR401 are four channel LVDS buffer/ repeaters capable of datarates of up to 2 Gbps. High speed data paths and flow-through pinout minimize internal device jitter and simplify board layout, while pre-emphasis overcomes ISI jitter effects from lossy backplanes and cables. The differential inputs interface to LVDS, and Bus LVDS signals such as those on National's 10-, 16-, and 18- bit Bus LVDS SerDes, as well as CML and LVPECL. The differential inputs and outputs of the DS15BR400 are internally terminated with 100Ω resistors to improve performance and minimize board space. The DS15BR401 does not have input termination resistors. The repeater function is especially useful for boosting signals for longer distance transmission over lossy cables and backplanes.

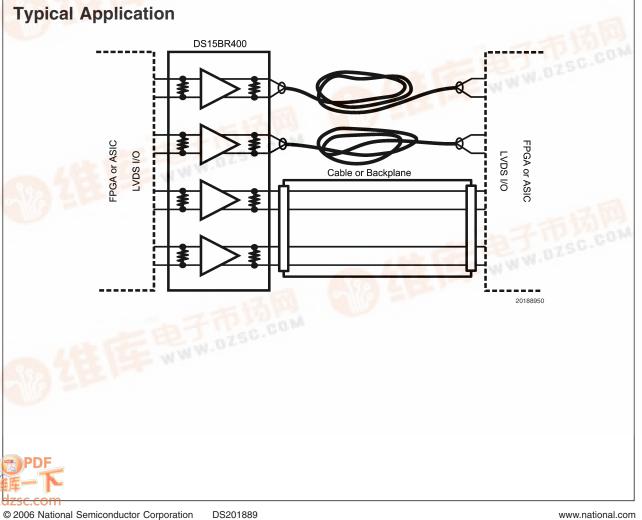
The DS15BR400/DS15BR401 are powered from a single 3.3V supply and consume 578 mW (typ). They operate over the full -40°C to +85°C industrial temperature range and are available in space saving LLP-32 and TQFP-48 packages.

Features

- DC to 2 Gbps low jitter, high noise immunity, low power operation
- 6 dB of pre-emphasis drives lossy backplanes and cables
- LVDS/CML/LVPECL compatible input, LVDS output
- \blacksquare On-chip 100 Ω output termination, optional 100 Ω input termination
- 15 kV ESD protection on LVDS inputs and outputs
- Single 3.3V supply
- Industrial -40 to +85°C temperature range
- Space saving LLP-32 or TQFP-48 packages
- Evaluation Kit Available

Applications

- Cable extention applications
- Signal repeating and buffering
- Digital routers



DS15BR400/DS15BR401

Block and Connection Diagrams PEM PWDN PEM PWDN Pre-emphasis and Control Pre-emphasis and Control OUT0+ OUT0+ IN0+ IN0+ IN0-OUT0-IN0-OUT0-OUT1+ OUT1+ IN1+ IN1+ IN1-OUT1-IN1-OUT1-IN2+ OUT2+ IN2+ OUT2+ IN2-OUT2-IN2-OUT2-OUT3+ OUT3+ IN3+ IN3+ OUT3-OUT3-IN3-IN3-20188903 20188901 DS15BR400 Block Diagram DS15BR401 Block Diagram PWDN PWDN GND VDD VDD V_{DD} V_{DD} PEM N/C П 8 7 6 5 4 3 2 1 11 10 9 8 7 6 5 4 3 2 12 1 13 IN0+ ſ 48 32 OUT0+ 0 IN0+ 9 47 🗖 OUT0-14 IN0- 🗖 10 31 OUT0-46 🗖 OUT1+ IN0-15 IN1+ 🗆 16 45 🗖 OUT1-IN1- **Г** 11] 30 OUT1+ IN1+ 44 🗖 GND GND 17 ſ DAP IN1-12] 29 OUT1-43 🗖 GND 18 GND C (GND) 19 42 OUT2+ 13 28 OUT2+ IN2+ IN2+ 20 41 DUT2-IN2- 🗖 IN2-14 27 OUT2-21 40 🗖 OUT3+ IN3+ 15 22 39 OUT3-26 OUT3+ IN3- 🗆 IN3+ GND 🗖 23 38 🗖 GND 16 25 OUT3-IN3-GND 🗖 24 37 🗖 GND 17 18 19 20 21 22 23 24 25 26 27 28 29 30 31 32 33 34 35 36 Vpp VDD N/C NC NC N/C Ŋ N/C 20188902 LLP Pinout - Top View **TQFP** Pinout - Top View

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Pin Name	TQFP Pin Number	LLP Pin Number	I/O, Type	Description
DIFFER	ENTIAL INPUTS			
IN0+	13	9	I, LVDS	Channel 0 inverting and non-inverting differential inputs.
IN0-	14	10		
IN1+	15	11	I, LVDS	Channel 1 inverting and non-inverting differential inputs.
IN1-	16	12		
IN2+	19	13	I, LVDS	Channel 2 inverting and non-inverting differential inputs.
IN2-	20	14		
IN3+	21	15	I, LVDS	Channel 3 inverting and non-inverting differential inputs.
IN3–	22	16		
DIFFER	ENTIAL OUTPUT	S		
OUT0+	48	32	O, LVDS	Channel 0 inverting and non-inverting differential outputs. (Note 2)
OUT0-	47	31		
OUT1+	46	30	O, LVDS	Channel 1 inverting and non-inverting differential outputs. (Note 2)
OUT1-	45	29		
OUT2+	42	28	O, LVDS	Channel 2 inverting and non-inverting differential outputs. (Note 2)
OUT2-	41	27		
OUT3+	40	26	O, LVDS	Channel 3 inverting and non-inverting differential outputs. (Note 2)
OUT3-	39	25		
	CONTROL INTE	RFACE		
PWDN	12	8	I, LVTTL	A logic low at PWDN activates the hardware power down mode (all channels).
PEM	2	2	I, LVTTL	Pre-emphasis Control Input (affects all Channels)
POWER				•
V _{DD}	3, 4, 5, 7, 10,	3, 4, 6, 7,	I, Power	V _{DD} = 3.3V, ±10%
	11, 28, 29, 32,	20, 21		
	33			
GND	8, 9, 17, 18, 23,	5 (Note 1)	I, Ground	Ground reference for LVDS and CMOS circuitry. For the LLP package, the
	24, 37, 38, 43,			DAP is used as the primary GND connection to the device in addition to the
	44			pin numbers listed. The DAP is the exposed metal contact at the bottom of
				the LLP-32 package. It should be connected to the ground plane with at
				least 4 vias for optimal AC and thermal performance.
N/C	1,6, 25, 26, 27,	1, 17,		No Connect
	30, 31, 34, 35,	18,19,22,		
	36	23, 24		

Note 1: Note that for the LLP package the GND is connected thru the DAP on the back side of the LLP package in addition to the actual pin numbers listed. Note 2: The LVDS outputs do not support a multidrop (BLVDS) environment. The LVDS output characteristics of the DS15BR400 and DS15BR401 are optimized for point-to-point backplane and cable applications.

Absolute Maximum Ratings (Note 3)

	-
Supply Voltage (V _{DD})	-0.3V to +4.0V
CMOS Input Voltage	–0.3V to (V _{DD} +0.3V)
LVDS Receiver Input Voltage	–0.3V to (V _{DD} +0.3V)
LVDS Driver Output Voltage	–0.3V to (V _{DD} +0.3V)
LVDS Output Short Circuit Current	+40 mA
Junction Temperature	+150°C
Storage Temperature	–65°C to +150°C
Lead Temperature (Solder, 4sec)	260°C
Max Pkg Power Capacity @ 25°C	
TQFP	1.64W
LLP	4.16W
Thermal Resistance (θ_{JA})	
TQFP	76°C/W
LLP	30°C/W
Package Derating above +25°C	
TQFP	13.2mW/°C
LLP	33.3mW/°C
ESD Last Passing Voltage	
HBM, 1.5kΩ, 100pF	8 kV

LVDS pins to GND only	15 kV
EIAJ, 0Ω, 200pF	250V
Charged Device Model	1000V

Recommended Operating Conditions

Supply Voltage (V _{CC})	3.0V to 3.6V
Input Voltage (V _I) (Note 4)	0V to V_{CC}
Output Voltage (V _O)	0V to V_{CC}
Operating Temperature (T _A)	
Industrial	–40°C to +85°C

Note 3: Absolute maximum ratings are those values beyond which damage to the device may occur. The databook specifications should be met, without exception, to ensure that the system design is reliable over its power supply, temperature, and output/input loading variables. National does not recommend operation of products outside of recommended operation conditions. **Note 4:** V_{ID} max < 2.4V

Electrical Characteristics

Over recommended operating supply and temperature ranges unless other specified.

Symbol	Parameter	Conditions	Min	Typ (Note 5)	Мах	Units
LVCMOS	DC SPECIFICATIONS (PWD	DN, PEM)	I	1		1
VIH	High Level Input Voltage		2.0		V_{DD}	V
VIL	Low Level Input Voltage		GND		0.8	V
I _{IH}	High Level Input Current	$V_{IN} = V_{DD} = 3.6V (\overline{PWDN} \text{ pin})$	-10		+10	μA
I _{IHR}	High Level Input Current	$V_{IN} = V_{DD} = 3.6V (PEM pin)$	40		200	μA
I _{IL}	Low Level Input Current	$V_{\rm IN} = V_{\rm SS}, V_{\rm DD} = 3.6 V$	-10		+10	μA
C _{IN1}	LVCMOS Input Capacitance	Any Digital Input Pin to V _{SS}		5.5		pF
V _{CL}	Input Clamp Voltage	$I_{CL} = -18 \text{ mA}, V_{DD} = 0 \text{V}$	-1.5	-0.8		V
LVDS IN	PUT DC SPECIFICATIONS (I	Nn±)	L L			
V _{TH}	Differential Input High Threshold (Note 6)	$V_{CM} = 0.8V$ to 3.55V, $V_{DD} = 3.6V$		0	100	mV
V _{TL}	Differential Input Low Threshold (Note 6)	$V_{CM} = 0.8V$ to 3.55V, $V_{DD} = 3.6V$	-100	0		mV
VID	Differential Input Voltage	$V_{CM} = 0.8V$ to 3.55V, $V_{DD} = 3.6V$	100		2400	mV
V _{CMR}	Common Mode Voltage Range	V _{ID} = 150 mV, V _{DD} = 3.6V	0.05		3.55	v
C _{IN2}	LVDS Input Capacitance	IN+ or IN– to V _{SS}		3.0		pF
I _{IN}	Input Current	V _{IN} = 3.6V, V _{DD} = 3.6V	-10		+10	μA
		$V_{IN} = 0V, V_{DD} = 3.6V$	-10		+10	μA

Cumhal	Deveneter	Conditions	Min	Typ	Max	L lus it o
Symbol Parameter		Conditions		(Note 5)	Max	Units
LVDS OI	JTPUT DC SPECIFICATIONS	(OUTn±)				
V _{od}	Differential Output Voltage, 0% Pre-emphasis (Note 6)	$R_{L} = 100\Omega$ external resistor between OUT+ and OUT- Figure 1		360	500	mV
ΔV _{OD}	Change in V _{OD} between Complementary States				35	mV
V _{os}	Offset Voltage (Note 7)			1.18	1.475	V
ΔV_{OS}	Change in V _{OS} between Complementary States		-35		35	mV
С _{оит}	LVDS Output Capacitance	OUT+ or OUT- to V _{SS}		2.5		pF
l _{os}	Output Short Circuit Current	OUT+ or OUT- Short to GND		-21	-40	mA
		OUT+ or OUT- Short to VDD		6	40	mA
SUPPLY	CURRENT (Static)	1				
сс	Supply Current	All inputs and outputs enabled and active, terminated with differential load of 100Ω between OUT+ and OUT PEM = L		175	215	mA
ccz	Supply Current - Power Down Mode	$\overline{PWDN} = L, PEM = L$		20	200	μA
SWITCH	ING CHARACTERISTICS—L	VDS OUTPUTS				
l _{lht}	Differential Low to High Transition Time (Note 12)	Use an alternating 1 and 0 pattern at 200 Mbps, measure between 20% and 80% of $\rm V_{OD}.$		170	250	ps
НЦТ	Differential High to Low Transition Time (Note 12)	Figures 2, 4		170	250	ps
PLHD	Differential Low to High Propagation Delay	Use an alternating 1 and 0 pattern at 200 Mbps, measure at 50% $V_{\rm OD}$ between input to output.		1.0	2.0	ns
PHLD	Differential High to Low Propagation Delay	Figures 2, 3		1.0	2.0	ns
SKD1	Pulse Skew (Note 12)	It _{PLHD} -t _{PHLD} I		10	60	ps
ѕксс	Output Channel to Channel Skew (Note 12)	Difference in propagation delay (t_{PLHD} or t_{PHLD}) among all output channels.		25	75	ps
SKP	Part to Part Skew (Note 12)	Common edge, parts at same temp and $V_{\rm CC}$			550	ps
JIT	Jitter (0% Pre-emphasis)	RJ - Alternating 1 and 0 at 750 MHz (Note 9)		0.5	1.5	ps
	(Note 8)	DJ - K28.5 Pattern, 1.5 Gbps (Note 10)		14	30	ps
		TJ - PRBS 2 ²³ -1 Pattern, 1.5 Gbps (Note 11)		14	31	ps
ON	LVDS Output Enable Time	Time from PWDN to OUT± change from TRI-STATE to active. Figures 5, 6			20	μs
OFF	LVDS Output Disable Time	Time from PWDN to OUT± change from active to TRI-STATE. Figures 5, 6			12	ns

Note 5: Typical parameters are measured at V_{DD} = 3.3V, T_A = 25°C. They are for reference purposes, and are not production-tested.

Note 6: Differential output voltage V_{OD} is defined as ABS(OUT+-OUT-). Differential input voltage V_{ID} is defined as ABS(IN+-IN-).

Note 7: Output offset voltage V_{OS} is defined as the average of the LVDS single-ended output voltages at logic high and logic low states.

Note 8: Jitter is not production tested, but guaranteed through characterization on a sample basis.

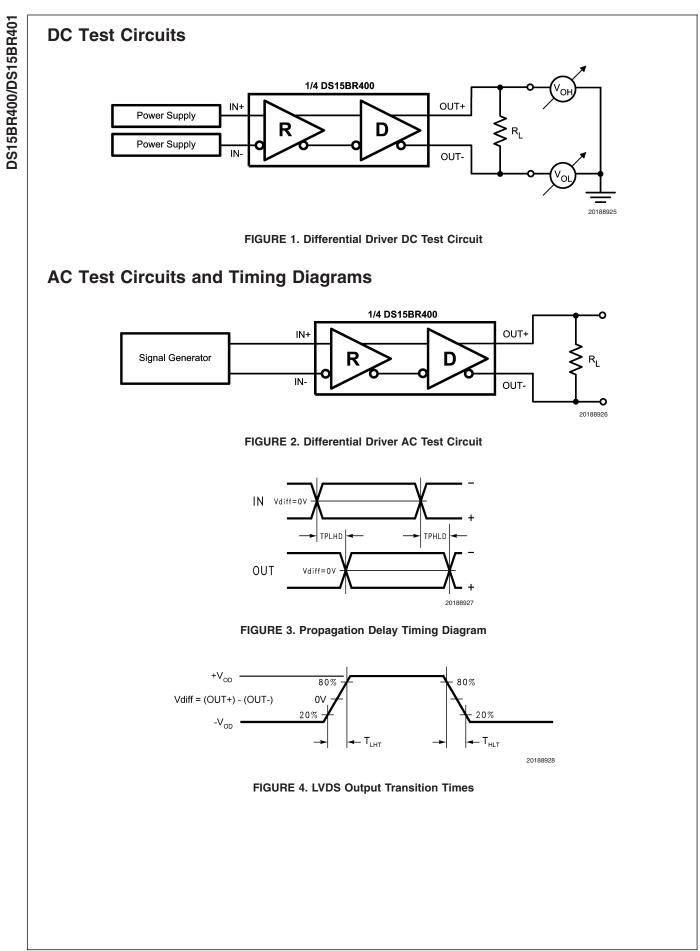
Note 9: Random Jitter, or RJ, is measured RMS with a histogram including 1500 histogram window hits. Stimulus and fixture Jitter has been subtracted. The input voltage = V_{ID} = 500 mV, input common mode voltage = V_{ICM} = 1.2V, 50% duty cycle at 750 MHz, $t_r = t_f = 50$ ps (20% to 80%).

Note 10: Deterministic Jitter, or DJ, is a peak to peak value. Stimulus and fixture jitter has been subtracted. The input voltage = V_{ID} = 500 mV, input common mode voltage = V_{ICM} = 1.2V, K28.5 pattern at 1.5 Gbps, t_r = t_f = 50 ps (20% to 80%). The K28.5 pattern is repeating bit streams of (001111010 1100000101).

Note 11: Total Jitter, or TJ, is measured peak to peak with a histogram including 3500 window hits. Stimulus and fixture Jitter has been subtracted. The input voltage = V_{ID} = 500 mV, input common mode voltage = V_{ICM} = 1.2V, 2²³-1 PRBS pattern at 1.5 Gbps, t_r = t_f = 50 ps (20% to 80%).

Note 12: Not production tested. Guaranteed by a statistical analysis on a sample basis at the time of characterization.

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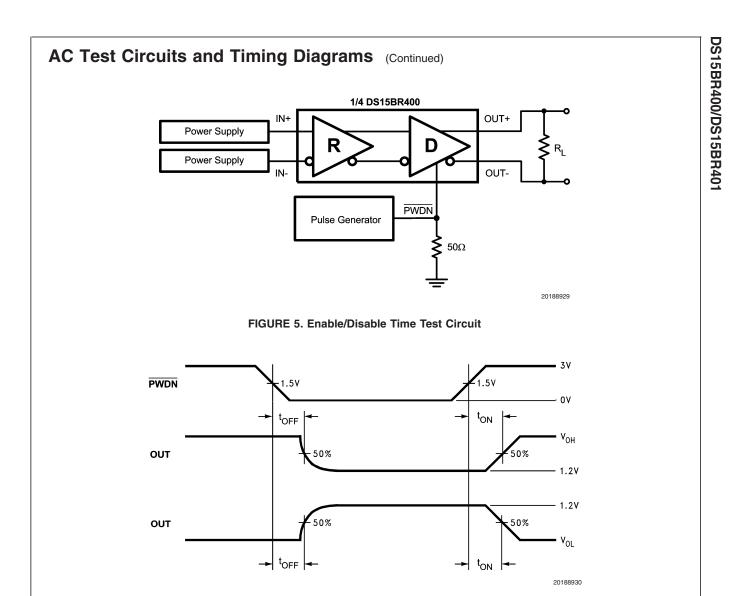


FIGURE 6. Enable/Disable Time Diagram

Application Information

INTERNAL TERMINATIONS

The DS15BR400 has integrated termination resistors on both the input and outputs. The inputs have a 100Ω resistor across the differential pair, placing the receiver termination as close as possible to the input stage of the device. The LVDS outputs also contain an integrated 100Ω ohm termination resistor, this resistor is used to minimize the output return loss and does not take the place of the 100 ohm termination at the inputs to the receiving device. The integrated terminations improve signal integrity and decrease the external component count resulting in space savings. The DS15BR401 has 100Ω output terminations only.

OUTPUT CHARACTERISTICS

The output characteristics of the DS15BRB400/DS15BR401 have been optimized for point-to-point backplane and cable applications, and are not intended for multipoint or multidrop signaling.

POWERDOWN MODE

The PWDN input activates a hardware powerdown mode. When the powerdown mode is active (PWDN=L), all input and output buffers and internal bias circuitry are powered off. When exiting powerdown mode, there is a delay associated with turning on bandgap references and input/output buffer circuits as indicated in the LVDS Output Switching Characteristics

PRE-EMPHASIS

Pre-emphasis dramatically reduces ISI jitter from long or lossy transmission media. One pin is used to select the pre-emphasis level for all outputs, off or on. The preemphasis boost is approximately 6 dB at 750 MHz.

Pre-emphasis Co	ontrol Selecti	on Table
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PEM	Pre-Emphasis
0	Off
1	On

INPUT FAILSAFE BIASING

External pull up and pull down resistors may be used to provide enough of an offset to enable an input failsafe under open-circuit conditions. This configuration ties the positive LVDS input pin to V_{DD} thru a pull up resistor and the negative LVDS input pin is tied to GND by a pull down resistor. The pull up and pull down resistors should be in the 5k Ω to 15k Ω range to minimize loading and waveform distortion to the driver. The common-mode bias point ideally should be set to approximately 1.2V. Please refer to application note AN-1194 "Failsafe Biasing of LVDS Interfaces" for more information.

DECOUPLING

Each power or ground lead of the DS15BR400 should be connected to the PCB through a low inductance path. For best results, one or more vias are used to connect a power or ground pin to the nearby plane. Ideally, via placement is immediately adjacent to the pin to avoid adding trace inductance. Placing power plane closer to the top of the board reduces effective via length and its associated inductance.

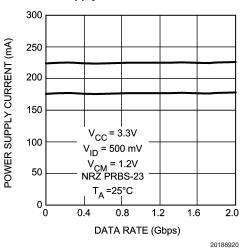
Bypass capacitors should be placed close to VDD pins. Small physical size capacitors, such as 0402, X7R, surface mount capacitors should be used to minimize body inductance of capacitors. Each bypass capacitor is connected to the power and ground plane through vias tangent to the pads of the capacitor. An X7R surface mount capacitor of size 0402 has about 0.5 nH of body inductance. At frequencies above 30 MHz or so, X7R capacitors behave as low impedance inductors. To extend the operating frequency range to a few hundred MHz, an array of different capacitor values like 100 pF, 1 nF, 0.03 μ F, and 0.1 μ F are commonly used in parallel. The most effective bypass capacitor can be built using sandwiched layers of power and ground at a separation of 2–3 mils. With a 2 mil FR4 dielectric, there is approximately 500 pF per square inch of PCB.

The center dap of the LLP package housing the DS15BR400 should be connected to a ground plane through an array of vias. The via array reduces the effective inductance to ground and enhances the thermal performance of the LLP package.

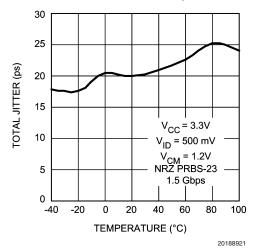
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Typical Performance Characteristics

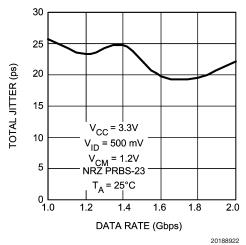
Power Supply Current vs. Data Rate



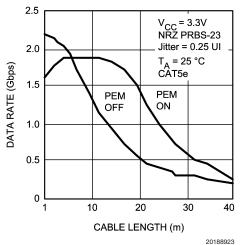
Total Jitter vs. Ambient Temperature



Total Jitter vs. Data Rate

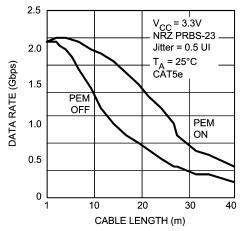


Data Rate vs. Cable Length (0.25 UI Criteria)



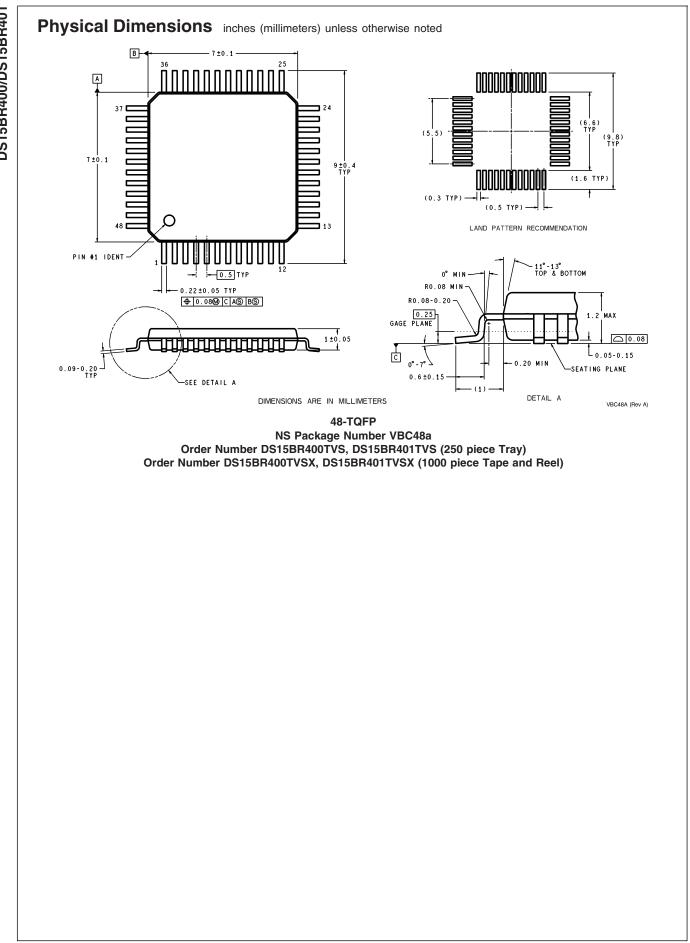
Data presented in this graph was collected using the DS15BR400EVK, a pair of RJ-45 to SMA adapter boards and various length Belden 1700a cables. The maximum data rate was determined based on total jitter (0.25 UI criteria) measured after the cable. The total jitter was a peak to peak value measured with a histogram including 3000 window hits.





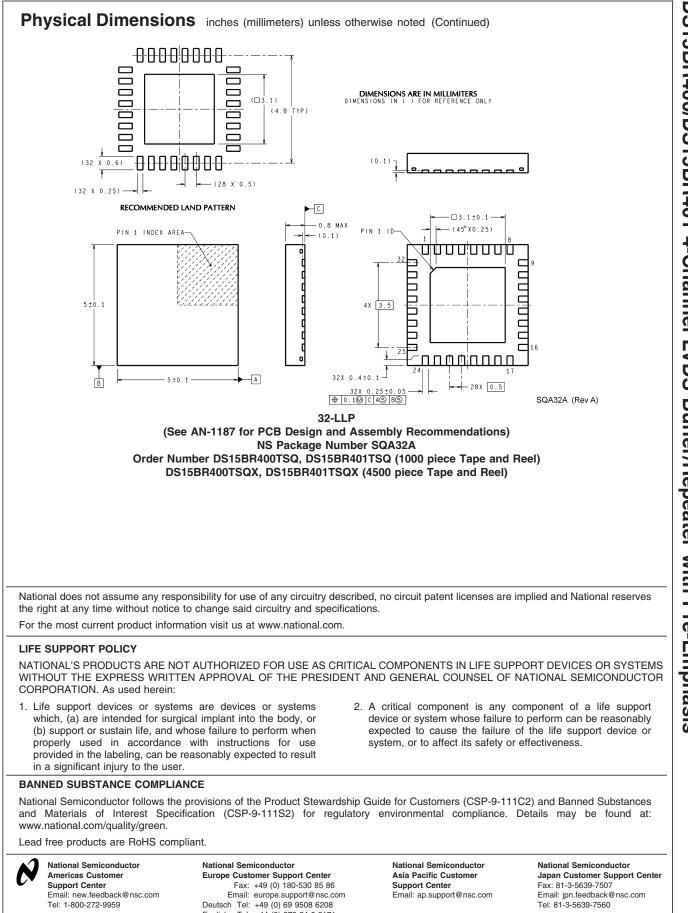
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Data presented in this graph was collected using the DS15BR400EVK, a pair of RJ-45 to SMA adapter boards and various length Belden 1700a cables. The maximum data rate was determined based on total jitter (0.5 UI criteria) measured after the cable. The total jitter was a peak to peak value measured with a histogram including 3000 window hits.



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